

REPLACEMENT CLAIMS

92. (Amended) A method for etching an oxide layer of a substrate, comprising:
placing a substrate having an oxide layer formed over said substrate into a reactive chamber;
introducing an etching gas into said reactive chamber;
generating a plasma of said etching gas at a first power level and contacting said oxide layer of said substrate with said first power level plasma for a first predetermined time; and
B1 generating a plasma of said etching gas at a second power level in said reactive chamber and contacting said oxide layer of said substrate with said second power level plasma for a second predetermined time to etch said oxide layer, wherein said first and second power levels are different.